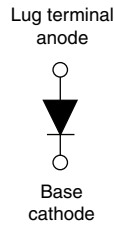


HEXFRED®

Ultrafast Soft Recovery Diode, 210 A


HALF-PAK (D-67)

FEATURES

- Very low Q_{rr} and t_{rr}
- Designed and qualified for industrial level
- UL approved file E222165
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Reduced snubbing

DESCRIPTION

HEXFRED® diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di_F/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

PRIMARY CHARACTERISTICS	
I_F (maximum)	210 A
V_R	400 V
$I_{F(DC)}$ at T_C	106 A at 100 °C
Package	HALF-PAK (D-67)
Circuit configuration	Single diode

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V_R		400	V
Continuous forward current	I_F	$T_C = 25\text{ °C}$	210	A
		$T_C = 100\text{ °C}$	106	
Single pulse forward current	I_{FSM}	Limited by junction temperature	600	
Non-repetitive avalanche energy	E_{AS}	$L = 100\text{ }\mu\text{H}$, duty cycle limited by maximum T_J	1.4	mJ
Maximum power dissipation	P_D	$T_C = 25\text{ °C}$	329	W
		$T_C = 100\text{ °C}$	132	
Operating junction and storage temperature range	T_J, T_{Stg}		-55 to +150	°C

ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	$I_R = 100\text{ }\mu\text{A}$	400	-	-	V
Maximum forward voltage	V_{FM}	$I_F = 90\text{ A}$	-	1.06	1.45	
		$I_F = 180\text{ A}$	-	1.2	1.67	
		$I_F = 90\text{ A}, T_J = 125\text{ °C}$	-	0.96	1.23	
Maximum reverse leakage current	I_{RM}	$T_J = 125\text{ °C}, V_R = 400\text{ V}$	See fig. 2	0.6	2	mA
Junction capacitance	C_T	$V_R = 200\text{ V}$	See fig. 3	180	260	pF
Series inductance	L_S	From top of terminal hole to mounting plane	-	7.0	-	nH



DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5	t _{rr}	T _J = 25 °C	I _F = 90 A di _F /dt = 200 A/μs V _R = 200 V	-	90	140	ns
		T _J = 125 °C		-	158	240	
Peak recovery current See fig. 6	I _{RRM}	T _J = 25 °C		-	9	17	A
		T _J = 125 °C		-	15	30	
Reverse recovery charge See fig. 7	Q _{rr}	T _J = 25 °C		-	420	1100	nC
		T _J = 125 °C		-	1200	3200	
Peak rate of recovery current See fig. 8	di _{(rec)M} /dt	T _J = 25 °C	-	370	-	A/μs	
		T _J = 125 °C	-	270	-		

THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55 to 150	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation See fig. 4	0.38	°C/W
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	0.05	
Approximate weight			30	g
			1.06	oz.
Mounting torque	minimum	Non-lubricated threads	3 (26.5)	N · m (lb · in)
	maximum		4 (35.4)	
Terminal torque	minimum	3.4 (30)		
	maximum	5 (44.2)		
Case style		HALF-PAK (D-67)		

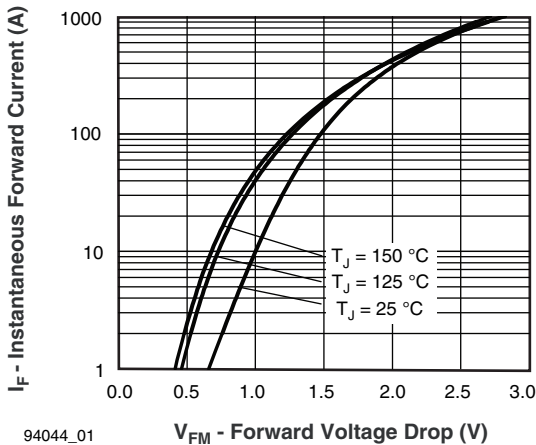


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

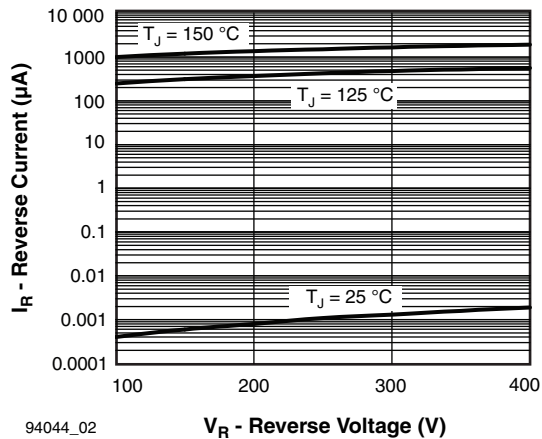


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

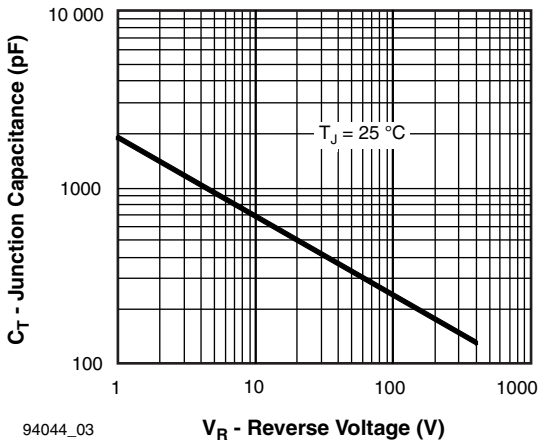


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

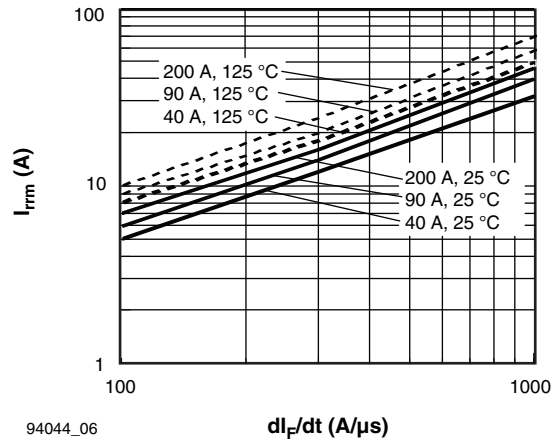


Fig. 6 - Typical Recovery Current vs. dI_F/dt

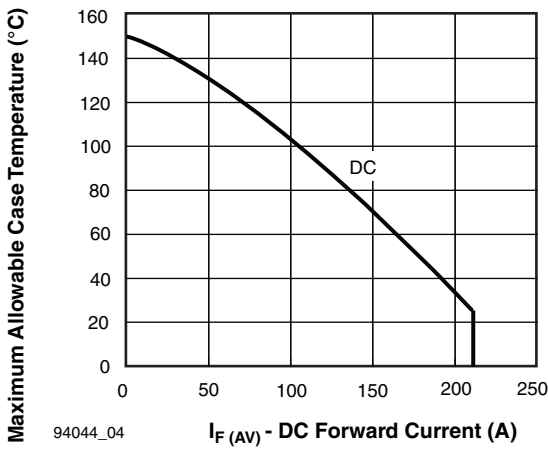


Fig. 4 - Maximum Allowable Case Temperature vs. DC Forward Current

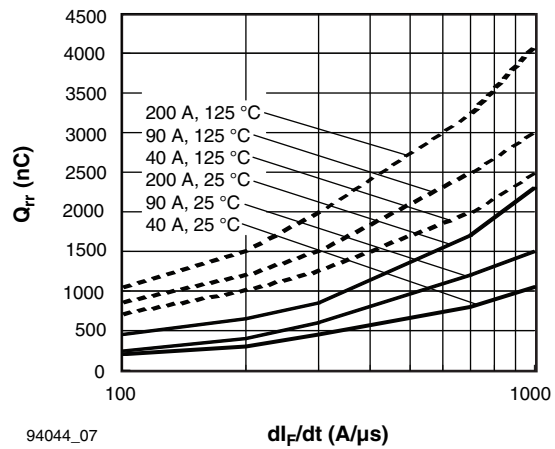


Fig. 7 - Typical Stored Charge vs. dI_F/dt

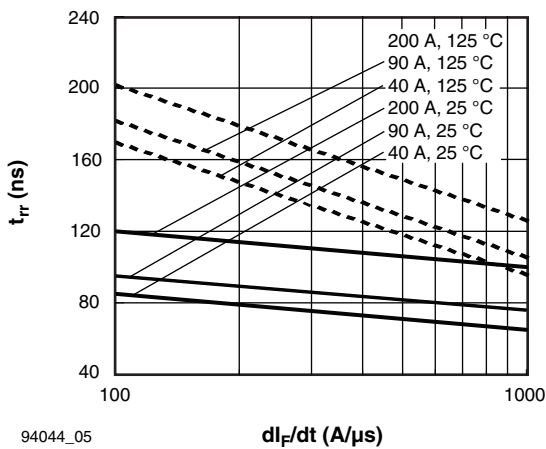


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt

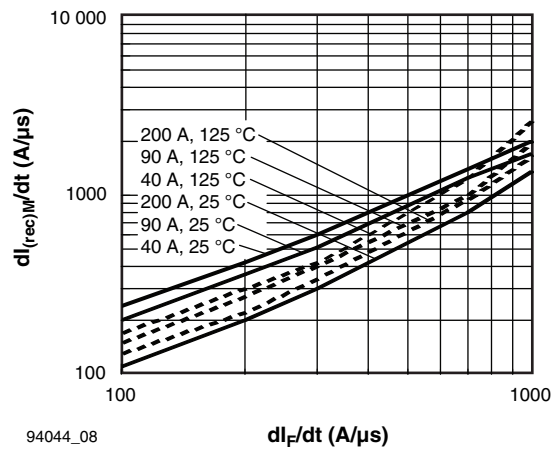


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

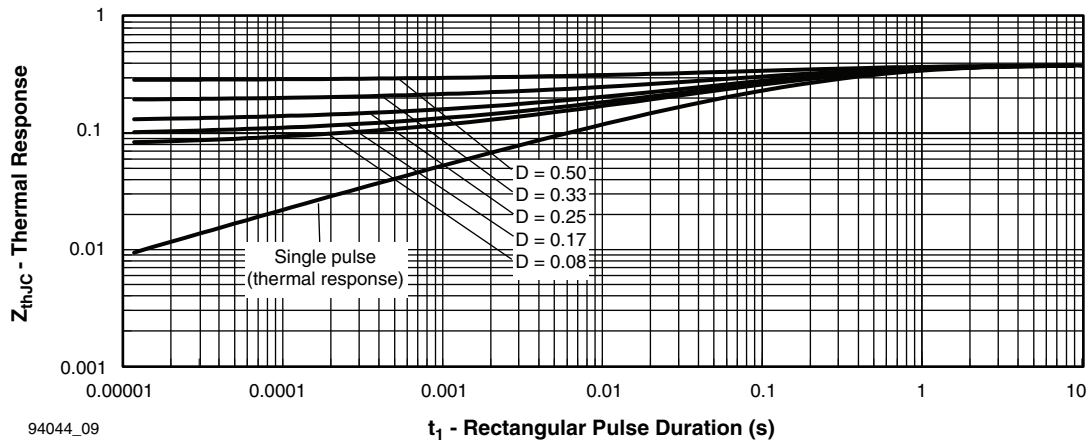


Fig. 9 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

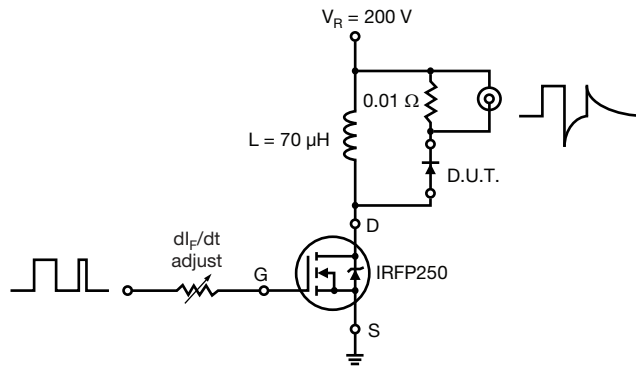
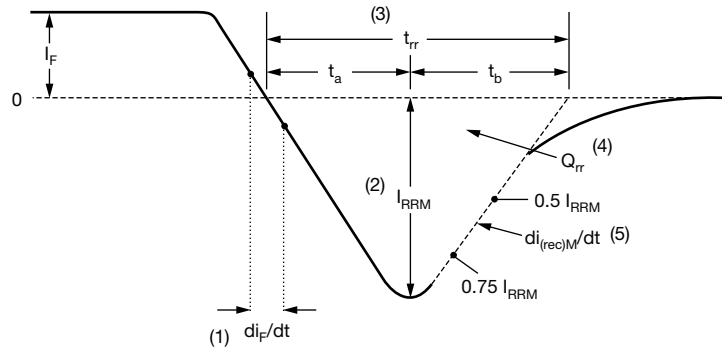


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt - rate of change of current through zero crossing
- (2) I_{RRM} - peak reverse recovery current
- (3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through $0.75 I_{RRM}$ and $0.5 I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}
- (5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

Fig. 11 - Reverse Recovery Waveform and Definitions

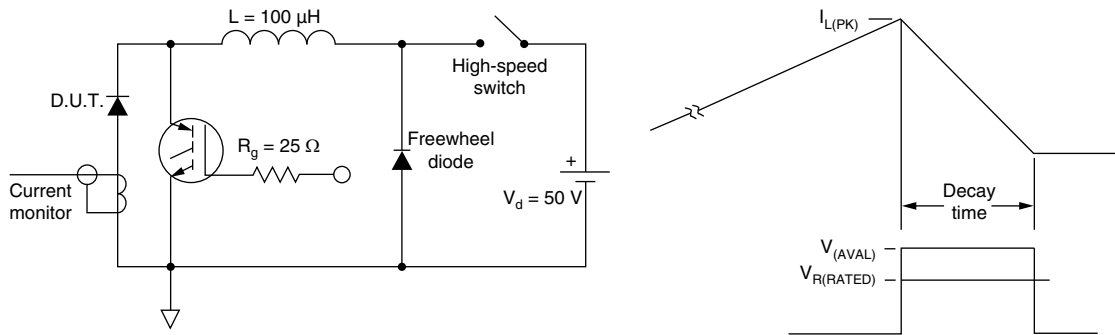


Fig. 12 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

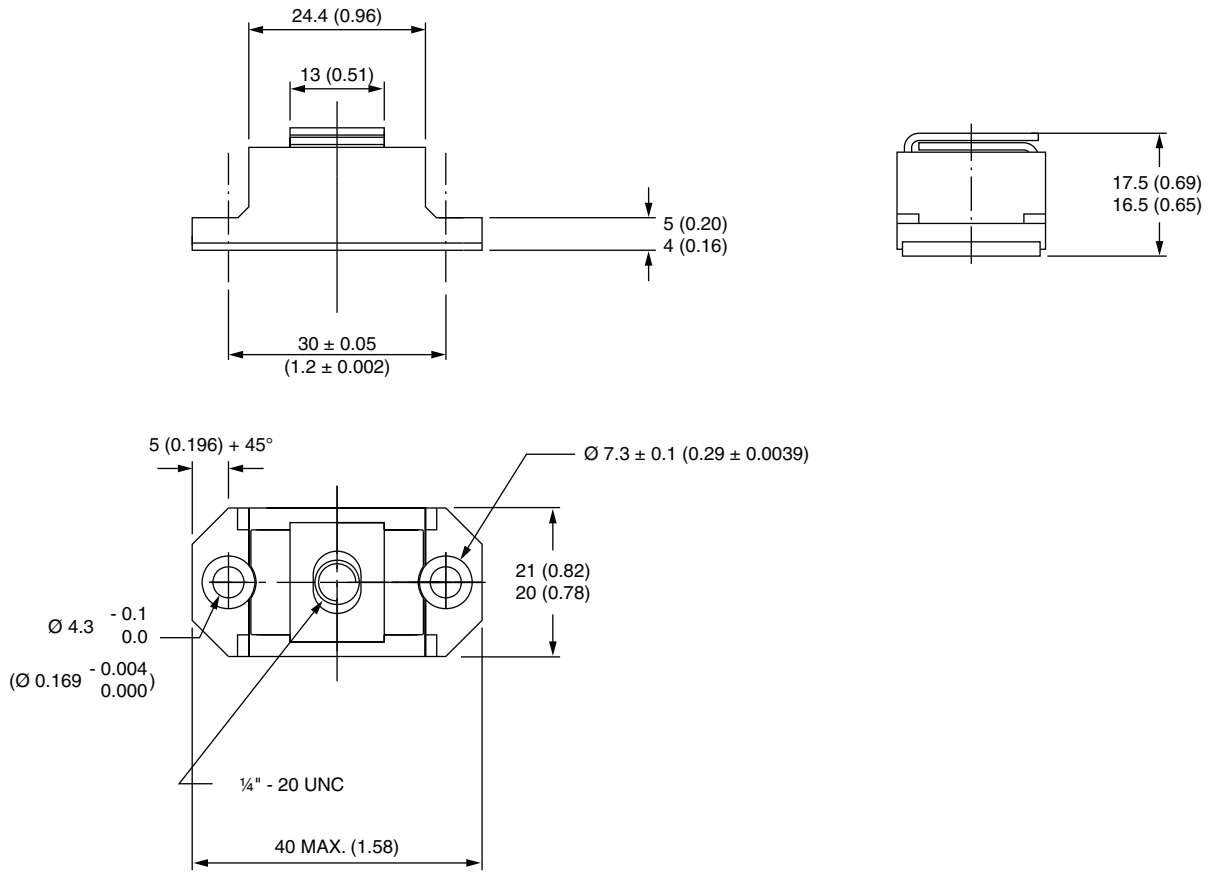
Device code	VS-	HFA	90	N	H	40	PbF
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - HEXFRED® family
- 3** - Average current rating
- 4** - N = not isolated
- 5** - H = HALF-PAK (D-67)
- 6** - Voltage rating (400 V)
- 7** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95020

D-67 HALF-PAK

DIMENSIONS in millimeters (inches)





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